

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	cool\$3.clm. and heat\$3.CLM. AND DEVELOP.CLM. AND RESIST.CLM. and temperature.clm. and humidity.clm. and control\$4.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:34
L2	0	cool\$3.clm. and heat\$3.CLM. AND DEVELOP.CLM. AND RESIST.CLM. and temperature.clm. and (dew humid\$3).clm. and control\$4.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:35
L3	1187	cool\$3.clm. and heat\$3.CLM. and temperature.clm. and (dew humid\$3).clm. and control\$4.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:36
L4	21	cool\$3.clm. and heat\$3.CLM. and temperature.clm. and (dew humid\$3).clm. and control\$4.clm. and resist.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:40
L5	6	cool\$3.clm. and heat\$3.CLM. and temperature.clm. and (dew humid\$3).clm. and control\$4.clm. and resist.clm. and point.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:40
L6	288	kitano-junichi.in. matsuyama-yuji.in. kitano-takahiro.in. matsui-hidefumi.in. suzuki-yo.in. yamashita-masami.in. aoyama-toru.in. iwaki-hiroyuki.in. shimura-satoru.in. deguchi-msatoshi.in. yoshihara-kousuke.in. iida-naruaki.in.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:47
L7	0	6 and (dew.clm. and "point.clm")	US-PGPUB; USPAT	OR	ON	2006/10/30 10:47
L8	0	6 and dew.clm. and point.clm.	US-PGPUB; USPAT	OR	ON	2006/10/30 10:47
S7	1	10/649,780	US-PGPUB; USPAT	OR	ON	2006/10/23 16:36
S8	131	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941.ccls.) and (resist and heat\$3 and cool\$3)	US-PGPUB; USPAT	OR	ON	2005/08/22 09:17
S9	22	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941.ccls.) and (reaction with inhibit\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S10	6	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941.ccls.) and (resist with resolution)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S11	217	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414/935-941.ccls.) and (resist and heat\$3 and cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S12	23	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414/935-941.ccls.) and (reaction with inhibit\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S13	7	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414/935-941.ccls.) and (resist with resolution)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S14	5	("6097469").URPN.	USPAT	OR	ON	2005/02/18 16:41
S15	1	("6632281").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 16:41
S16	6	("5725664" "5785741" "5876280" "5952149" "6054181" "6467976").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/18 16:43
S17	23	("5725664").URPN.	USPAT	OR	ON	2005/02/18 16:49
S18	3	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941.ccls.) and (resist same (inhibit\$3 prevent\$3) same cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:12
S19	892	(resist same (inhibit\$3 prevent\$3) same cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:12
S20	114	(resist same (inhibit\$3 prevent\$3) same cool\$3 same transfer\$4)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:49
S21	9	("5970717").URPN.	USPAT	OR	ON	2005/02/18 17:31
S22	75	(resist same (inhibit\$3 prevent\$3) same transfer\$4) and "118"/\$.ccls.	US-PGPUB; USPAT	OR	ON	2005/02/18 17:50
S23	61	S22 not S20	US-PGPUB; USPAT	OR	ON	2005/02/18 17:50

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S24	2	"09076685"	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:32
S25	157	tateyama-kiyohisa.in.	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:31
S26	0	"9076685"	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:32
S27	1	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941.ccls.) and (dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:11
S28	3	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414/935-941.ccls.) and (dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:13
S29	13	(substrate wafer semiconductor workpiece) and (resist same dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:37
S30	121	(substrate wafer semiconductor workpiece) and ("resolution reaction")	US-PGPUB; USPAT	OR	ON	2005/02/21 14:45
S31	4	resist same ("resolution reaction")	US-PGPUB; USPAT	OR	ON	2005/02/21 14:46
S32	2	resist same ("resolution reaction")	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:50
S33	1657482	transfer\$4 convey\$4 transport\$4 mov\$4 with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:51
S34	85	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:52
S35	9	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:45
S36	39	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 15:19
S37	6	(resist) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 15:29
S38	5	("5254170" "5609689" "6143083" "6224274" "6235634").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 15:25
S39	3	(resist) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:30
S40	0	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:30
S41	0	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S42	2	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S43	882	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S44	84	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:33
S45	276	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:32
S46	2	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist with cool\$3	US-PGPUB; USPAT	OR	ON	2005/02/21 15:33
S47	0	(acid with amplif\$7) with (cool\$3) with resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:34

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S48	3	(acid with amplif\$7) with (cool\$3) with resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:34
S49	16	(acid with amplif\$7) same (cool\$3) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:44
S50	96	(resolv\$3 resolution solubilization) same (cool\$3) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:45
S51	18	("5151871").URPN.	USPAT	OR	ON	2005/02/21 16:26
S52	1	("6414276").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/21 16:26
S53	11	("4518848" "5452177" "5538758" "5595241" "5730803" "5775416" "5811762" "6072163" "6080969" "6091060" "6270580").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 16:26
S54	248	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:45
S55	738	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 17:46
S56	808	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 17:47
S57	283	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:47
S58	5	((transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) same resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 19:01
S59	16	((transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 17:55
S60	120	((transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) and resist	US-PGPUB; USPAT	OR	ON	2005/02/21 17:56
S61	104	S60 not S59	US-PGPUB; USPAT	OR	ON	2005/02/21 17:56
S62	5	("4717645" "4924800" "4985722" "5339128" "5401316").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 18:46
S63	4	("6022672").URPN.	USPAT	OR	ON	2005/02/21 18:49
S64	1	118/69.ccls. and (((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction) same resist)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:03
S65	133	118/69.ccls. and (((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3))	US-PGPUB; USPAT	OR	ON	2005/02/21 19:03
S66	3	118/69.ccls. and (((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with resist))	US-PGPUB; USPAT	OR	ON	2005/02/21 19:04
S67	133	118/69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:05
S68	0	118/69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with reaction)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:05
S69	5	118/58-69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with reaction)	US-PGPUB; USPAT	OR	ON	2005/02/22 13:29
S70	325	118/58-69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:08

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S71	45	118/58-69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3) and resist	US-PGPUB; USPAT	OR	ON	2005/02/21 19:35
S72	325	118/58-69.ccls. and ((hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:36
S73	1	("6022672").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/22 09:38
S74	54	(US-20010013161-\$ or US-20010014372-\$ or US-20020009813-\$ or US-20020034595-\$ or US-20020037462-\$ or US-20020187423-\$ or US-20030035087-\$ or US-20030114010-\$ or US-20040050321-\$ or US-20040229441-\$).did. or (US-4855000-\$ or US-4913090-\$ or US-4985722-\$ or US-5151871-\$ or US-5297910-\$ or US-5339128-\$ or US-5547328-\$ or US-5565034-\$ or US-5639301-\$ or US-5686224-\$ or US-5725664-\$ or US-5942013-\$ or US-5970717-\$ or US-5972110-\$ or US-6022672-\$ or US-6077350-\$ or US-6097469-\$ or US-6099643-\$ or US-6183358-\$ or US-6215545-\$ or US-6224274-\$ or US-6261365-\$ or US-6292250-\$ or US-6319322-\$ or US-6341903-\$ or US-6364762-\$).did. or (US-6372042-\$ or US-6414276-\$ or US-6444029-\$ or US-6464789-\$ or US-6485203-\$ or US-6499777-\$ or US-6558053-\$ or US-6572457-\$ or US-6573031-\$ or US-6632281-\$ or US-6676757-\$ or US-6717113-\$).did. or (JP-04021773-\$ or JP-10256344-\$ or JP-10256345-\$ or JP-11031732-\$ or JP-2001308005-\$).did. or (US-20040050321-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/02/22 09:39
S75	26	S74 and align\$3	US-PGPUB; USPAT	OR	ON	2005/02/22 11:59
S76	18	S74 and (align\$3 same expos\$4)	US-PGPUB; USPAT	OR	ON	2005/02/22 09:39
S77	6	S74 and dehumid\$7	US-PGPUB; USPAT	OR	ON	2005/02/22 11:16
S78	0	(118/719.ccls. 156/345.31.ccls. "156"/.45.32.ccls.) and (dehumid\$7 with (transfer\$4 transport\$4 convey\$4))	US-PGPUB; USPAT	OR	ON	2005/02/22 11:16
S79	0	(118/719.ccls. 156/345.31.ccls. "156"/345.32.ccls.) and (dehumid\$7 with (transfer\$4 transport\$4 convey\$4))	US-PGPUB; USPAT	OR	ON	2005/02/22 11:17
S80	20	dehumid\$7 with (transfer\$4 transport\$4 convey\$4) with (wafer substrate semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/22 11:17
S81	17	dehumid\$7 with (transfer\$4 transport\$4 convey\$4) with (wafer substrate semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/22 11:28
S82	1	("5932380").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/22 11:55
S83	2377	aligner with expos\$3	EPO; JPO; DERWENT	OR	ON	2005/02/22 11:56
S84	17	S74 and (interface with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
S85	8773	(interface with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
S86	69	("interface section" with cooling)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
S87	94	("interface section" with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 13:08
S88	48	(118/715-733.ccls. 156/345.\$ccls.) and (cool\$3 with gas with regulat\$3 with (moisture temperature humidity))	US-PGPUB; USPAT	OR	ON	2005/02/22 13:37
S89	1	118/58-69.ccls. and (cool\$3 with gas with regulat\$3 with (moisture temperature humidity))	US-PGPUB; USPAT	OR	ON	2005/02/22 13:30

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S90	200	kitano-junichi.in. matsuyama-yuji.in. kitano-takahiro.in. matsui-hidefumi.in. suzuki-yo.in. yamashita-masami.in. aoyama-toru.in. iwaki-hiroyuki.in. shimura-satoru.in. deguchi-msatoshi.in. yoshihara-kousuke.in. iida-naruaki.in.	US-PGPUB; USPAT	OR	ON	2005/02/22 14:51
S91	57	S90 and (humid\$7 dehumid\$7 moisture)	US-PGPUB; USPAT	OR	ON	2005/08/22 09:17
S92	17	S90 and (humid\$7 dehumid\$7 moisture).clm.	US-PGPUB; USPAT	OR	ON	2005/02/22 15:06
S93	1	("6632281").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/22 15:06
S94	139	(interface with (section station chamber) with (cool\$3 chill\$3) with (plate platen support susceptor holder))	US-PGPUB; USPAT	OR	ON	2005/08/17 20:36
S95	35	(interface with (section station chamber) with (cool\$3 chill\$3) with (plate platen support susceptor holder)) and resist	US-PGPUB; USPAT	OR	ON	2005/08/17 15:50
S96	1	(interface with (section station chamber) with (cool\$3 chill\$3) with (plate platen support susceptor holder)) and resist	EPO; JPO; DERWENT	OR	ON	2005/08/17 15:51
S97	2	(interface with (section station chamber) with (cool\$3 chill\$3 rest\$3 wait\$3 heat\$3 inhibit\$3 reduc\$3 retard\$5 prevent\$3 prevent\$3) with (plate platen support susceptor holder)) and resist	EPO; JPO; DERWENT	OR	ON	2005/08/17 15:52
S98	10	(interface with (section station chamber) with (cool\$3 chill\$3 rest\$3 wait\$3 heat\$3 inhibit\$3 reduc\$3 retard\$5 prevent\$3 prevent\$3) with (plate platen support susceptor holder)) and (coat\$3 deposit\$3)	EPO; JPO; DERWENT	OR	ON	2005/08/17 15:55
S99	4	(interface with (section station chamber unit) with (cool\$3 chill\$3 rest\$3 wait\$3 heat\$3 inhibit\$3 reduc\$3 retard\$5 prevent\$3 prevent\$3)) and ((coat\$3 deposit\$3) with resist)	EPO; JPO; DERWENT	OR	ON	2005/08/17 16:00
S100	371	(interface with (section station chamber unit) with (cool\$3 chill\$3 rest\$3 wait\$3 heat\$3 inhibit\$3 reduc\$3 retard\$5 prevent\$3 prevent\$3)) and ((coat\$3 deposit\$3) with resist)	US-PGPUB; USPAT	OR	ON	2005/08/17 16:01
S101	19	(interface with (section station chamber unit) with (cool\$3 chill\$3 rest\$3 wait\$3 heat\$3) with (inhibit\$3 reduc\$3 retard\$5 prevent\$3 prevent\$3)) and ((coat\$3 deposit\$3) with resist)	US-PGPUB; USPAT	OR	ON	2005/08/17 16:09
S102	5	(interface with (section station chamber unit) with (cool\$3 chill\$3) with (inhibit\$3 retard\$5 prevent\$3 prevent\$3) with reaction)	US-PGPUB; USPAT	OR	ON	2005/08/17 16:11
S103	0	(interface with (section station chamber unit) with (cool\$3 chill\$3) with (inhibit\$3 retard\$5 prevent\$3 prevent\$3) with reaction)	EPO; JPO; DERWENT	OR	ON	2005/08/17 16:10
S104	303	((section station chamber unit) with (cool\$3 chill\$3) with (inhibit\$3 retard\$5 prevent\$3 prevent\$3) with reaction)	US-PGPUB; USPAT	OR	ON	2005/08/17 16:12
S105	19	((section station chamber unit) with ((cool\$3 chill\$3) with plate) with (inhibit\$3 retard\$5 prevent\$3 prevent\$3) with reaction)	US-PGPUB; USPAT	OR	ON	2005/08/17 16:14
S106	19	((section station chamber unit) with ((cool\$3 chill\$3)) with (inhibit\$3 retard\$5 prevent\$3 prevent\$3) with reaction) and resist	US-PGPUB; USPAT	OR	ON	2005/08/17 16:15
S107	116	"430"/\$.ccls. and (interface with (cool\$3 chill\$3))	US-PGPUB; USPAT	OR	ON	2005/08/17 20:21
S108	1	("6814809").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/30 10:33
S109	4	("20020025375" "5939130" "6126703" "6147329").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/17 20:31
S110	0	("6814809").URPN.	USPAT	OR	ON	2005/08/17 20:30

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S11 1	3	("5570994" "5664154" "6056998").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/17 20:57
S11 2	230	kitano-junichi.in. matsuyama-yuji.in. kitano-takahiro.in. matsui-hidefumi.in. suzuki-yo.in. yamashita-masami.in. aoyama-toru.in. iwaki-hiroyuki.in. shimura-satoru.in. deguchi-msatoshi.in. yoshihara-kousuke.in. iida-naruaki.in.	US-PGPUB; USPAT	OR	ON	2005/08/22 09:17
S11 3	68	S112 and (humid\$7 dehumid\$7 moisture)	US-PGPUB; USPAT	OR	ON	2005/08/22 09:17
S11 4	147	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls. 414-935-941. ccls.) and (resist and heat\$3 and cool\$3)	US-PGPUB; USPAT	OR	ON	2005/08/22 09:17
S11 5	1	10/649,780	US-PGPUB; USPAT	OR	ON	2005/12/15 10:32
S11 6	5100	resist\$4 with control\$4 with area	US-PGPUB; USPAT	OR	ON	2006/03/31 19:23
S11 7	75	resist\$4 with control\$4 with area with (cool\$3 chill\$3)	US-PGPUB; USPAT	OR	ON	2006/03/31 19:35
S11 8	1	"09772923"	US-PGPUB; USPAT	OR	ON	2006/03/31 19:32
S11 9	26	resist\$4 with control\$4 with area with (cool\$3 chill\$3)	EPO; JPO; DERWENT	OR	ON	2006/03/31 19:35
S12 0	74	(US-20040050321-\$ or US-20030114010-\$ or US-20020009813-\$ or US-20010014372-\$ or US-20010013161-\$ or US-20020187423-\$ or US-20020034595-\$ or US-20020037462-\$ or US-20030035087-\$ or US-20040229441-\$ or US-20050042555-\$ or US-20020025375-\$).did. or (US-5725664-\$ or US-6632281-\$ or US-4855000-\$ or US-6097469-\$ or US-6573031-\$ or US-6364762-\$ or US-6215545-\$ or US-5942013-\$ or US-6183358-\$ or US-6444029-\$ or US-5297910-\$ or US-6099643-\$ or US-6077350-\$ or US-6224274-\$ or US-6676757-\$ or US-5565034-\$ or US-6464789-\$ or US-6292250-\$ or US-5547328-\$ or US-6499777-\$ or US-6558053-\$ or US-5970717-\$ or US-6485203-\$ or US-5972110-\$ or US-4913090-\$ or US-6572457-\$).did. or (US-6341903-\$ or US-6022672-\$ or US-5686224-\$ or US-5151871-\$ or US-6717113-\$ or US-6414276-\$ or US-6319322-\$ or US-5339128-\$ or US-4985722-\$ or US-6261365-\$ or US-5639301-\$ or US-6372042-\$ or US-5932380-\$ or US-6814809-\$ or US-6466300-\$ or US-6893805-\$ or US-6309116-\$ or US-4806225-\$ or US-5273585-\$ or US-6162591-\$ or US-6106167-\$ or US-6831258-\$ or US-6126703-\$ or US-5051338-\$ or US-4897337-\$ or US-5723259-\$).did. or (EP-275126-\$).did. or (JP-04021773-\$ or JP-10256345-\$ or JP-10256344-\$ or JP-2001176784-\$ or JP-11031732-\$ or JP-2001308005-\$ or JP-10335418-\$).did. or (US-20040050321-\$ or JP-04247695-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/10/23 13:04
S12 1	3	S120 and (dew with point)	US-PGPUB; USPAT	OR	ON	2006/10/23 13:05
S12 2	18	(118/719.ccls. 156/345.31.ccls. 156/345.32.ccls.) and (dew with point)	US-PGPUB; USPAT	OR	ON	2006/10/23 13:11
S12 3	10	(118/715-733.ccls. 156/345.\$ccls.) and (dew with point with control\$4)	US-PGPUB; USPAT	OR	ON	2006/10/23 13:13
S12 4	9	(c23c016\$.ipc. h01I021.ipc. c23f001\$.ipc.) and (dew and point and control\$4)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:16
S12 5	2397	(dew and point and control\$4)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:17
S12 6	102	S125 and (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:17

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S12 7	35	(dew with point with control\$4) same (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:39
S12 8	93	(dew with point with control\$4) same (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2006/10/23 13:19
S12 9	34	S128 and resist	US-PGPUB; USPAT	OR	ON	2006/10/23 13:20
S13 0	99	(dew with point) and control\$4 and (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:29
S13 1	70	(dew with point) and control\$4 and (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2006/10/23 13:29
S13 2	2447	(dew with point) and control\$4 and (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2006/10/23 13:29
S13 3	1	("5167714").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/23 13:37
S13 4	17	("5167714").URPN.	USPAT	OR	ON	2006/10/23 13:37
S13 5	10	("3336463" "3951340" "4174902" "4357900" "4367787" "4554887" "4561380" "4895733" "4919073").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/23 13:38
S14 0	10	("3336463" "3951340" "4174902" "4357900" "4367787" "4554887" "4561380" "4895733" "4919073").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/23 13:42
S14 1	5	S140 and humid\$5	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/23 14:21
S14 2	1	("6279650").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/23 14:21
S14 3	12	("2284914" "2419119" "2545491" "3415313" "3424231" "4711294" "5590532").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/23 14:21
S14 4	3	("6279650").URPN.	USPAT	OR	ON	2006/10/23 14:29
S14 5	1	("6126312").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/23 14:38
S14 6	11	("4245506" "4683258" "4696796" "4920451" "5079272" "5136274" "5296819" "5317274" "5533393" "5546802" "5767687").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/10/23 14:38
S14 7	3	("6126312").URPN.	USPAT	OR	ON	2006/10/23 14:41
S14 8	18	(374/28.ccls.) and (semiconductor wafer substrate) and (apparatus chamber section unit reactor)	US-PGPUB; USPAT	OR	ON	2006/10/23 14:45
S14 9	0	(374/28.ccls.) and (118/715-733.ccls.ccls. 156/345.\$ccls.)	US-PGPUB; USPAT	OR	ON	2006/10/23 14:46
S15 0	0	(374/28.ccls.) and (118/715-733.ccls. 156/345.\$ccls.)	US-PGPUB; USPAT	OR	ON	2006/10/23 14:46
S15 1	0	(374/28.ccls.) and ("438"/\$.ccls.)	US-PGPUB; USPAT	OR	ON	2006/10/23 14:46
S15 2	0	(374/28.ccls.) and ((coat\$3 deposit\$3) with resist)	US-PGPUB; USPAT	OR	ON	2006/10/23 14:47
S15 3	1	10/649,780	US-PGPUB; USPAT	OR	ON	2006/10/23 16:36
S15 4	1	S153 and (resist with gas)	US-PGPUB; USPAT	OR	ON	2006/10/23 17:16
S15 5	1	("6632681").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/23 16:46

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S15 6	1	("6632281").PN.	US-PGPUB; USPAT	OR	OFF	2006/10/23 16:46
S15 7	1	S153 and (temperature with chill)	US-PGPUB; USPAT	OR	ON	2006/10/23 17:18
S15 8	1	S153 and (temperature with interface)	US-PGPUB; USPAT	OR	ON	2006/10/23 17:18